

a layer of undoped silicate glass disposed over the patterned oxide layer and having a physical contour of recessed and extended portions corresponding to the physical contour of the oxide layer;

a layer of doped silicate glass over the layer of undoped silicate glass and having a physical contour of recessed and extended portions corresponding to the physical contour of the layer of undoped silicate glass; and

a first substantially planar layer of dielectric material covering at least one or more of the recessed portions of the layer of the doped silicate glass, and exposing at least one or more of the extended portions of the layer of the doped silicate glass layer.

21. (New) The device of claim 20, further comprising:

a second layer of dielectric material covering the first substantially planar layer of dielectric material and being in direct contact with the at least one or more extended portions of the layer of the doped silicate glass layer.

22. (New) The device of claim 21 wherein the layer of doped silicate glass is a layer of borophosphorous silicate glass.

23. (New) The device of claim 22 wherein the first layer of dielectric material is a layer of plasma-enhanced tetraethyl orthosilicate.

24. (New) The device of claim 23 wherein the second layer of dielectric material is a layer of plasma-enhanced tetraethyl orthosilicate.

25. (New) The device of claim 24 wherein the second layer of dielectric material is substantially planar.

26. (New) The device of claim 25 wherein the layer of borophosphorous silicate glass has a thickness between approximately 2k and 8k angstroms.